

Title	Engineering Prototype Report for EP-91 – 12 W Power Supply using TinySwitch®-III (TNY278P)	
Specification	85-265 VAC Input, 12 V, 1 A Output	
Application	TinySwitch-III Reference Design (DAK-91)	
Author	Power Integrations Applications Department	
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Revision	1.1	

## **Summary and Features**

- EcoSmart® Meets all existing and proposed harmonized energy efficiency standards including: CECP (China), CEC, EPA, AGO, European Commission
  - No-load consumption 140 mW at 265 VAC (no bias winding required)
  - > 75% active-mode efficiency (exceeds standards requirement of 71%)
- BP/M capacitor value selects MOSFET current limit for greater design flexibility
- Output overvoltage protection (OVP) using primary bias winding sensed shutdown feature
- Tightly toleranced I<sup>2</sup>f parameter (–10%, +12%) reduces system cost:
  - Increases MOSFET and magnetics power delivery
  - Reduces overload power, which lowers output diode and capacitor costs
- Integrated TinySwitch-III Safety/Reliability features:
  - Accurate (± 5%), auto-recovering, hysteretic thermal shutdown function maintains safe PCB temperatures under all conditions
  - Auto-restart protects against output short circuit and open loop fault conditions
  - > 3.2 mm creepage on package enables reliable operation in high humidity and high pollution environments
- Meets EN550022 and CISPR-22 Class B conducted EMI with >12 dBµV margin
- Meets IEC61000-4-5 Class 3 AC line surge

The products and applications illustrated herein (including circuits external to the products and transformer construction) may be covered by one or more U.S. and foreign patents or potentially by pending U.S. and foreign patent applications assigned to Power Integrations. A complete list of Power Integrations' patents may be found at www.powerint.com.

ı		or Contents	
1		oduction	
2	Pow	ver Supply Specification	6
3	Circ	uit Diagram	7
4	Circ	uit Description	8
	4.1	Input Rectification and Filtering	8
	4.2	TNY278P Operation	
	4.3	Output Rectification and Filtering	g
	4.4	Feedback and Output Voltage Regulation	
	4.5	Output Overvoltage Shutdown	
	4.6	EMI Design Aspects	
	4.7	Peak Primary Current Limit Selection	
	4.8	UV Lockout	
5	PCE	3 Layout	11
6	Bill	Of Materials	12
7	Trai	nsformer Specification	13
	7.1	Electrical Diagram	
	7.2	Electrical Specifications	13
	7.3	Materials	14
	7.4	Transformer Build Diagram	14
	7.5	Transformer Construction	15
8		nsformer Spreadsheet	
9	Perl	formance Data	18
	9.1	Efficiency	18
	9.2	Active Mode CEC Measurement Data	
	9.3	No-load Input Power (R8 not installed: no bias winding supplementation)	
	9.4	No-load Input Power (with R8 and bias winding supplementation)	
	9.5	Available Standby Output Power	
	9.6	Regulation	
	9.6.		
1(		rmal Performance	
1		veforms	
	11.1		
	11.2	Output Voltage Start-Up Profile	
	11.3	Drain Voltage and Current Start-Up Profile	
		Load Transient Response (75% to 100% Load Step)	
	11.5	Output Ripple Measurements	27
	11.5	11	
	11.5		
	11.6	Overvoltage Shutdown	
		e Surge	
1:		nducted EMI	
		115 VAC, Full Load	
,		230 VAC, Full Load	
14	4 Auc	lible Noise	32



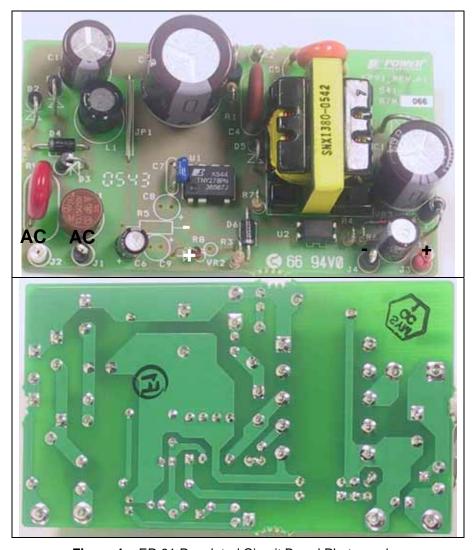
15	Extended and Reduced Current Limit (I <sub>LIMIT</sub> ) Operation	33
	TNY277 and TNY279 Operation in EP-91	
	OVP Operation Verification	
	Revision History	

# **Important Note:**

Although this board was designed to satisfy safety isolation requirements, it has not been agency approved. Therefore, all testing should be performed using an isolation transformer to provide the AC input to the power supply.

# 1 Introduction

This report describes a universal input, 12 V, 1 A flyback power supply using a TNY278P device from the *TinySwitch-III* family of ICs. It contains the complete specification of the power supply, a detailed circuit diagram, the entire bill of materials required to build the supply, extensive documentation of the power transformer, along with test data and oscillographs of the most important electrical waveforms. The board provides a number of user configurable options which are designed to demonstrate the features and flexibility of the *TinySwitch-III* family. These include easy adjustment of the device current limit for increased output power or higher efficiency operation, and a latched output overvoltage shutdown.



**Figure 1** – EP-91 Populated Circuit Board Photographs.

# 2 Power Supply Specification

Description	Symbol	Min	Тур	Max	Units	Comment
Input Voltage Frequency No-load Input Power (230 VAC) No-load Input Power (230 VAC) Output	V <sub>IN</sub> f <sub>LINE</sub>	85 47	50/60	265 64 0.15 0.05	VAC Hz W W	2 Wire – no P.E.  w/o UVLO resistor or bias winding With bias winding support
Output Voltage Output Ripple Voltage Output Current	V <sub>OUT</sub> V <sub>RIPPLE</sub> I <sub>OUT</sub>	11 1	12	13 100	V mV A	± 8% 20 MHz bandwidth
Total Output Power Continuous Output Power Overvoltage Shutdown	P <sub>out</sub> V <sub>ov</sub>	12 15		18	W V	With bias sense
Efficiency Full Load Required average efficiency at 25, 50, 75 and 100 % of P <sub>OUT</sub>	η η <sub>CEC</sub>	75 71.3			% %	Measured at P <sub>OUT</sub> 25 °C Per CEC / Energy Star STDs, with TNY278 & standard current limit
Environmental Conducted EMI Safety		Meets CISPR22B / EN55022B Designed to meet IEC950, UL1950 Class II				
Surge (Differential)		1			kV	1.2/50 μs surge, IEC 1000-4-5, Series Impedance:
Surge (Common mode)		2			kV	Differential Mode: $2 \Omega$ Common Mode: $12 \Omega$
Ambient Temperature	T <sub>AMB</sub>	0		50	°C	Free convection, sea level

# 3 Circuit Diagram

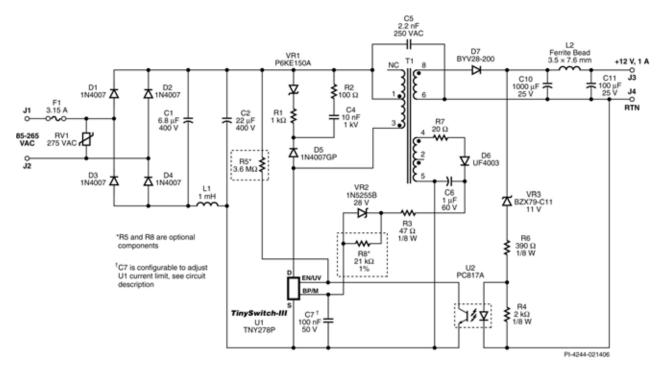


Figure 2 - EP-91 Circuit Diagram.

# 4 Circuit Description

This flyback power supply was designed around the TNY278P (U1 in Figure 2). The output voltage is sensed and fed back to U1 through optocoupler U2. That feedback is used by U1 to maintain constant voltage (CV) regulation of the output.

## 4.1 Input Rectification and Filtering

Diodes D1–D4 rectify the AC input. Capacitors C1 and C2 filter the rectified DC. Inductor L1, C1 and C2 form a pi filter that attenuates differential mode conducted EMI.

### 4.2 TNY278P Operation

The TNY278P device (U1) integrates an oscillator, a switch controller, startup and protection circuitry, and a power MOSFET, all on one monolithic IC.

One side of the power transformer (T1) primary winding is connected to the positive leg of C2, and the other side is connected to the DRAIN pin of U1. At the start of a switching cycle, the controller turns the MOSFET on, and current ramps up in the primary winding, which stores energy in the core of the transformer. When that current reaches the limit threshold, the controller turns the MOSFET off. Due to the phasing of the transformer windings and the orientation of the output diode, the stored energy then induces a voltage across the secondary winding, which forward biases the output diode, and the stored energy is delivered to the output capacitor. When the MOSFET turns off, the leakage inductance of the transformer induces a voltage spike on the drain node. The amplitude of that spike is limited by an RCD clamp network that consists of D5, C4 and R2. Resistor R1 and VR1 provide hard clamping of the drain voltage, only conducting during output overload. Resistor R2 also limits the reverse current that flows through D5 when the MOSFET turns on. This allows a slow, low-cost, glass passivated diode (with a recovery time of  $\leq 2 \mu s$ .) to be used for D5, which improves conducted EMI and efficiency.

Using ON/OFF control, U1 skips switching cycles to regulate the output voltage, based on feedback to its EN/UV pin. The EN/UV pin current is sampled, just prior to each switching cycle, to determine if that switching cycle should be enabled or disabled. If the EN/UV pin current is <115  $\mu A$ , the next switching cycle begins, and is terminated when the current through the MOSFET reaches the internal current limit threshold. To evenly spread switching cycles, preventing group pulsing, the EN pin threshold current is modulated between 115  $\mu A$  and 60  $\mu A$  based on the state during the previous cycle. A state-machine within the controller adjusts the MOSFET current limit threshold to one of four levels, depending on the load being demanded from the supply. As the load on the supply drops, the current limit threshold is reduced. This ensures that the effective switching frequency stays above the audible range until the transformer flux density is low. When the standard production technique of dip varnishing is used for the transformer, audible noise is practically eliminated.

### 4.3 Output Rectification and Filtering

Diode D7 rectifies the output of T1. Output voltage ripple was minimized by using a low ESR capacitor for C10 (see Section 6 for component part numbers and values). A post filter (ferrite bead L2 and C11) attenuates the high frequency switching noise.

### 4.4 Feedback and Output Voltage Regulation

The supply's output voltage regulation set point is set by the voltage that develops across Zener diode VR3, R6 and the LED in opto-coupler U2. The value of R4 was calculated to bias VR3 to about 0.5 mA when it goes into reverse avalanche conduction. This ensures that it is operating close to its rated knee current. Resistor R6 limits the maximum current during load transients. The values of R4 and R6 can both be varied slightly to fine-tune the output regulation set point. When the output voltage rises above the set point, the LED in U2 becomes forward biased. On the primary side, the photo-transistor of U2 turns on and draws current out of the EN/UV pin of U1. Just before the start of each switching cycle, the controller checks the EN/UV pin current. If the current flowing out of the EN/UV pin is greater than 115  $\mu$ A, that switching cycle will be disabled. As switching cycles are enabled and disabled, the output voltage is kept very close to the regulation set point. For greater output voltage regulation accuracy, a reference IC such as a TL431 can be used in place of VR3.

## 4.5 Output Overvoltage Shutdown

The *TinySwitch-III* family of ICs can detect overvoltage on the output of the supply and latch off. This protects the load in an open feedback loop fault condition, such as the failure of the optocoupler. Overvoltage on the output is detected through the BP/M pin and the bias winding on the transformer. The bias winding voltage is determined by the reflection of the output voltage through the turns ratio of the transformer. Therefore, an overvoltage on the output will be reflected onto the bias winding. The overvoltage threshold is the sum of the breakdown voltage of Zener diode VR2 and the BP/M pin voltage (28 V + 5.8 V). If the output voltage becomes abnormally high, the voltage on the bias winding will exceed the threshold voltage and excess current will flow into the BP/M pin. The latching shutdown circuit is activated when current into the BP/M pin exceeds 5 mA. Resetting a latched shutdown requires removing the AC input from the supply long enough to allow the input capacitors (C1 and C2) to discharge, and the BP/M pin voltage to drop below 2 V. Resistors R7 and R3 provide additional filtering of the bias voltage, with R3 also limiting the maximum current into the BYPASS pin in an OV condition

### 4.6 EMI Design Aspects

An input pi filter (C1, L1 and C2) attenuates conducted, differential mode EMI noise. Shielding techniques (*E-Shield*™) were used in the construction of T1 to reduce common mode EMI displacement currents. Resistor R2 and capacitor C4 dampen out some of the high frequency ringing that occurs when the MOSFET turns off. When combined with the IC's frequency jitter function, these techniques produce excellent conducted and radiated EMI performance (see Section 12 of this report).



# 4.7 Peak Primary Current Limit Selection

The value of the capacitor installed on the BP/M pin allows the current limit of U1 to be selected. The power supply designer can change the current limit of the MOSFET by simply changing the capacitance value connected to the BP/M pin (see the *TinySwitch-III* data sheet for more details).

- Installing a 0.1 μF capacitor on the BP/M pin selects the standard current limit of the IC, and is the normal choice for enclosed adapter applications.
- Installing a 1 μF capacitor on the BP/M pin reduces the MOSFET current limit, which lowers conduction losses and improves efficiency (at the expense of reducing the maximum power capability of the IC).
- A 10 μF capacitor on the BP/M pin will raise the MOSFET current limit and extend the power capability of the IC (for higher power applications that do not have the thermal constraints of an enclosed adapter, or to supply short-duration, peak load demands).

The EP91 demonstration board comes with a 0.1  $\mu$ F capacitor installed as C7, which causes U1 to select the standard current limit specified in the *TinySwitch-III* data sheet. If C7 were replaced by a 1  $\mu$ F capacitor (C8 in the BOM, section 6), the current limit of U1 will be the same as the standard current limit for a TNY277 device. If a 10  $\mu$ F capacitor is installed, the current limit of U1 will be the same as the standard current limit for a TNY279 device. The flexibility of this option enables the designer to do three things. First, it allows the designer to measure the effect of switching to an adjacent device without actually removing and replacing the IC. Second, it allows a larger device to be used with a lower current limit, for higher efficiency. Third, it allows a smaller device to be used with a higher current limit in a design when higher power is not required on a continual basis, which effectively lowers the cost of the supply.

#### 4.8 UV Lockout

The EP91 circuit board has a location where an optional under-voltage (UV) lockout detection resistor (R5) can be installed. When installed, MOSFET switching is disabled at startup until current into the EN/UV pin exceeds 25  $\mu$ A. This allows the designer to set the input voltage at which MOSFET switching will be enabled by choosing the value of R5. For example, a value of 3.6 M $\Omega$  requires an input voltage of 65 VAC (92 VDC across C2) before the current into the EN/UV pin exceeds 25  $\mu$ A. The UV detect function also prevents the output of the power supply from glitching (trying to restart) after output regulation is lost (during shutdown), by disabling MOSFET switching until the input voltage rises above the under-voltage lockout threshold.

# 5 PCB Layout

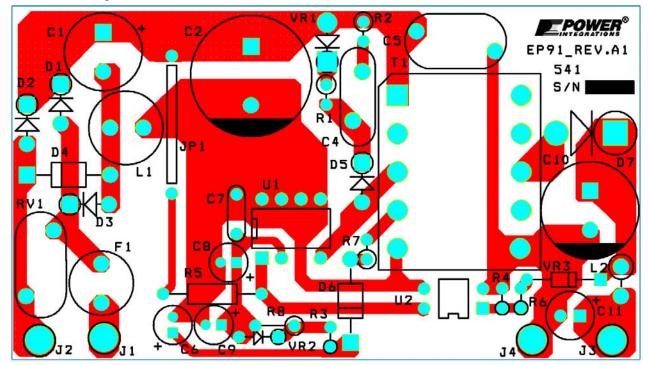


Figure 3 – Printed Circuit Board Layout (3.2 × 1.8 inches).

# 6 Bill Of Materials

Item	Qty	Part Ref Value Description		Mfg Part Number	Mfg	
1	1	C1	6.8 μF	6.8 μF, 400 V, Electrolytic, (10 x 16) EKXG401ELL6R8MJ16S		United Chemi-Con
2	1	C2	22 μF	22 μF, 400 V, Electrolytic, Low EKMX401ELL220ML20S ESR, 901 m $\Omega$ , (16 x 20)		United Chemi-Con
3	1	C4	10 nF	10 nF, 1 kV, Disc Ceramic	5HKMS10	Vishay
4	1	C5	2.2 nF	2.2 nF, Ceramic, Y1	440LD22	Vishay
5	1	C7	100 nF	100 nF, 50 V, Ceramic, X7R	B37987F5104K000 / ECU- S1H104KBB	Epcos/ Panasonic
6	2	C6, C8*	1 μF	1 μF, 50 V, Electrolytic, Gen. Purpose, (5 x 11)	EKMG500ELL1R0ME11D	United Chemi-Con
7	1	C9*	10 μF	10 μF, 50 V, Electrolytic, Gen. Purpose, (5 x 11)	EKMG500ELL100ME11D	United Chemi-Con
8	1	C10	1000 μF	1000 μF, 25 V, Electrolytic, Very Low ESR, 21 mΩ, (12.5 x 20)	EKZE250ELL102MK20S	United Chemi-Con
9	1	C11	100 μF	100 μF, 25 V, Electrolytic, Very Low ESR, 130 m $\Omega$ , (6.3 x 11)	EKZE250ELL101MF11D	United Chemi-Con
10	4	D1 D2 D3 D4	1N4007	1000 V, 1 A, Rectifier, DO-41	1N4007	Vishay
11	1	D5	1N4007GP	1000 V, 1 A, Rectifier, Glass Passivated, 2 us, DO-41	1N4007GP	Vishay
12	1	D6	UF4003	200 V, 1 A, Ultrafast Recovery, 50 ns, DO-41	UF4003	Vishay
13	1	D7	BYV28-200	200 V, 3.5 A, Ultrafast Recovery, 25 ns, SOD64	BYV28-200	Vishay
14	1	F1	3.15 A	3.15 A, 250V,Fast, TR5	3701315041	Wickman
15	2	J1 J4		Test Point, Black, Thru-hole mount	5011	Keystone
16	1	J2		Test Point, White, Thru-hole mount	5012	Keystone
17	1	J3		Test Point, Red, Thru-hole mount	5010	Keystone
18	1	JP1		Wire Jumper, Insulated, 24 AWG	KSW24W-0100	OK Indust.
19	1	L1	1 mH	1mH, 350 mA	HTB2-102-281	CUI
20	1	L2	Ferrite Bead	3.5 mm x 7.6 mm, 75 $\Omega$ at 25 MHz, 22 AWG hole, Ferrite Bead	2743004112	Fair-Rite
21	1	R1	1 kΩ	1 kΩ, 5%, 1/4 W, Carbon Film	CFR-25JB-1K0	Yageo
22	1	R2	100 Ω	100 Ω, 5%, 1/4 W, Carbon Film	CFR-25JB-100R	Yageo
23	1	R3	47 Ω	47 Ω, 5%, 1/8 W, Carbon Film	CFR-12JB-47R	Yageo
24	1	R4	2 kΩ	2 kΩ, 5%, 1/8 W, Carbon Film	CFR-12JB-2K0	Yageo
25	1	R5*	$3.6~\mathrm{M}\Omega$	3.6 MΩ, 5%, 1/2 W, Carbon Film	CFR-50JB-3M6	Yageo
26	1	R6	390 Ω	390 Ω, 5%, 1/8 W, Carbon Film	CFR-12JB-390R	Yageo
27	1	R7	20 Ω	20 Ω, 5%, 1/4 W, Carbon Film	CFR-25JB-20R	Yageo
28	1	R8*	21 kΩ	21 kΩ, 1%, 1/4 W, Metal Film	MFR-25FBF-21K0	Yageo
29	1	RV1	275 VAC	275 V, 45 J, 10 mm, Radial	V275LA10	Littlefuse
30	1	T1	EE25 Core	Bobbin, EE25, Vertical, 10 pins  Complete Assembly	YW-360-02B SNX-1380 LSPA20544 CWS-T1-EP91 SIL6038	Yih-Hwa Enterprises Santronics LiShin CWS Hical
31	1	U1	TNY278P	TinySwitch-III, TNY278P, DIP-8C TNY278P		Power Integrations
32	1	U2	PC817A	Optocoupler, 35 V, CTR 80-160%, ISP817A, PC817X1 4-DIP		Isocom, Sharp
33	1	VR1	P6KE150A	150 V, 5 W, 5%, TVS, DO204AC P6KE150A (DO-15)		Vishay
34	1	VR2	1N5255B	28 V, 500 mW, 5%, DO-35	1N5255B	Microsemi
35	1	VR3	BZX79-B11	11 V, 500 mW, 2%, DO-35	BZX79-B11	Vishay

<sup>\*</sup> Optional components

# 7 Transformer Specification

# 7.1 Electrical Diagram

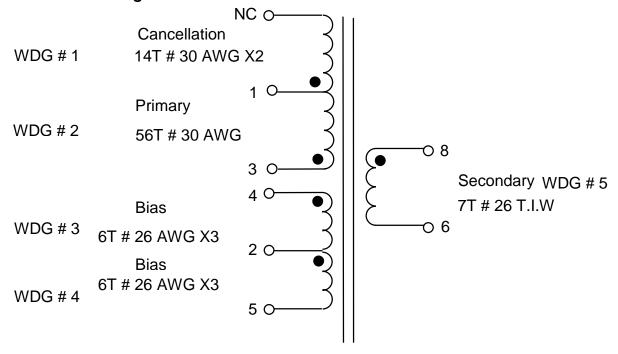


Figure 4 – Transformer Electrical Diagram.

# 7.2 Electrical Specifications

Electrical Strength	1 second, 60 Hz, from Pins 1-5 to Pins 6-10	3000 VAC
Primary Inductance	Pins 1-3, all other windings open, measured at 100 kHz, 0.4 V RMS	1050 μH, ±10%
Resonant Frequency	Pins 1-3, all other windings open	500 kHz (Min.)
Primary Leakage Inductance	Pins 1-3, with Pins 6-8 shorted, measured at 100 kHz, 0.4 V RMS	50 μH (Max.)

## 7.3 Materials

Item	Description					
[1]	Core: PC40EE25-Z, TDK or equivalent Gapped for A <sub>L</sub> of 335 nH/T <sup>2</sup>					
[2]	Bobbin: EE25, Vertical, 10 pin – Yih-Hwa part # YW-360-02B					
[3]	Magnet Wire: #30 AWG					
[4]	Magnet Wire: #26 AWG					
[5]	Triple Insulated Wire: #26 AWG.					
[6]	Tape: 3M # 44 Polyester web. 2.0 mm wide					
[7]	Tape: 3M 1298 Polyester Film, 2.0 mils thick, 8.6 mm wide					
[8]	Tape: 3M 1298 Polyester Film, 2.0 mils thick, 10.7 mm wide					
[9]	Tape: 3M 1298 Polyester Film, 2.0 mils thick, 4.0 mm wide					
[10]	Varnish (applied by dipping only, not vacuum impregnation)					

# 7.4 Transformer Build Diagram

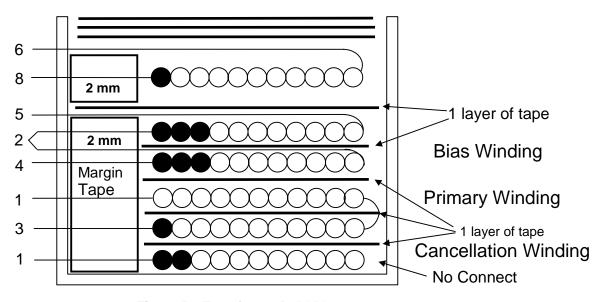


Figure 5 – Transformer Build Diagram.

# 7.5 Transformer Construction

Bobbin Set Up Orientation	Set up the bobbin with its pins oriented to the left hand side.
Margin Tape	Apply 2.0 mm margin at the pin side of bobbin using item [6]. Match combined height of shield, primary, and bias windings.
WD1 Cancellation Winding	Start at Pin 1. Wind 14 bifilar turns of item [3] from left to right. Wind with tight tension across entire bobbin evenly. Cut the ends of the bifilar and leave floating.
Insulation	1 Layer of tape [7] for insulation.
WD#2 Primary winding	Start at pin 3. Wind 28 turns of item [3] from left to right. Apply 1 Layer of tape [7] for insulation. Wind another 28 turns from right to left. Wind with tight tension across entire bobbin evenly. Finish at Pin 1.
Insulation	1 Layer of tape [7] for insulation.
WD #3 Bias Winding	Start at Pin 4, wind 6 trifilar turns of item [5]. Wind from left to right with tight tension. Wind uniformly, in a single layer across entire width of bobbin. Finish on Pin 2.
Insulation	1 Layer of tape [7] for insulation.
WD #4 Bias Winding	Start at Pin 2, wind 6 trifilar turns of item [5] from left to right with tight tension. Wind uniformly, in a single layer across entire width of bobbin. Finish on Pin 5.
Insulation	1 Layer of tape [8] for insulation.
Margin Tape	Apply 2.0 mm margin at the pin side of bobbin using item [6]. Match combined height of secondary windings.
WD #5 Secondary Winding	Start at Pin 8, wind 7 turns of item [5] from left to right. Wind uniformly, in a single layer across entire bobbin evenly. Finish on Pin 6.
Outer Insulation	3 Layers of tape [8] for insulation.
Core Assembly	Assemble and secure core halves using item [1] and item [9]
Varnish	Dip varnish using item [10] (do not vacuum impregnate)



# 8 Transformer Spreadsheet

ACDC_TinySwitch-III	INPUT	INFO	OUTPUT	UNIT	ACDC_TinySwitch-III_011906_Rev0-27.xls;
_011906; Rev.0.27;					TinySwitch-III Continuous/Discontinuous
Copyright Power					Flyback Transformer Design Spreadsheet
Integrations 2006	LADI EO				EDO4 40 V 4 A Huberra el la mer
ENTER APPLICATION VAR				\	EP91 - 12 V, 1 A, Universal Input
VACMIN VACMAX	85			Volts Volts	Minimum AC Input Voltage
	265				Maximum AC Input Voltage
fL	50			Hertz	AC Mains Frequency
VO	12.00			Volts	Output Voltage (at continuous power)
Ю	1.00			Amps	Power Supply Output Current (corresponding to
			40	107 11	peak power)
Power	0.74		12	Watts	Continuous Output Power
n	0.71				Efficiency Estimate at output terminals. Unter 0.7 if
7	0.50				no better data available Z Factor. Ratio of secondary side losses to the total
Z	0.50				losses in the power supply. Use 0.5 if no better data
					available
tC	3.00			mSeconds	Bridge Rectifier Conduction Time Estimate
CIN	28.80		20.0	uFarads	Input Capacitance
CIN	20.00		20.0	игагацъ	при Сараспансе
ENTER TinySwitch-III VAR					
TinySwitch-III	TNY278		TNY278		User defined TinySwitch-III
Chosen Device		TNY278			
Chose Configuration	STD		Standard		Enter "RED" for reduced current limit (sealed
			Current Limit		adapters), "STD" for standard current limt or "INC"
					for increased current limit (peak or higher power
					applications)
ILIMITMIN				Amps	Minimum Current Limit
ILIMITTYP			0.550	Amps	
ILIMITMAX			0.588	Amps	Maximum Current Limit
fSmin			124000		Minimum Device Switching Frequency
I^2fmin			35.937	A^2kHz	I^2f (product of current limit squared and frequency
V65	101.00				is trimmed for tighter tolerance)
VOR	101.00		101	Volts	Reflected Output Voltage (VOR < 135 V
V 50					Recommended)
VDS				Volts	TinySwitch-III on-state Drain to Source Voltage
VD				Volts	Output Winding Diode Forward Voltage Drop
KP			0.60		Ripple to Peak Current Ratio (KP < 6)
KP_TRANSIENT			0.38		Transient Ripple to Peak Current Ratio. Ensure
					KP_TRANSIENT > 0.25
<b>ENTER BIAS WINDING VA</b>	RIABLES				
VB			22.00	Volts	Bias Winding Voltage
NB			12.13		Bias Winding Number of Turns
VZOV			28.00		Over Voltage Protection zener diode.
			20.00		stage : retection block diodo.
LIVLO VARIARI ES					
UVLO VARIABLES V_UV_TARGET	92		92.00	Volto	Target under-voltage threshold, above which the
V_UV_TARGET	92		92.00	VOILS	power supply with start
V_UV_ACTUAL			92.20	Valta	Typical start-up voltage based on standard value of
V_UV_ACTUAL			92.20	VOILS	RUV ACTUAL
RUV IDEAL			3 50	Mohms	Calculated value for UV Lockout resistor
RUV_IDEAL RUV_ACTUAL				Mohms	Closest standard value of resistor to RUV IDEAL
NOV_ACTUAL			ა.ის	IVIUIIIII	Ciosest Statituatu value di 18515tol to ROV_IDEAL
ENTER TRANSPORT	005/00::0=	NIOT: CT.	(ADIAD: =0		
ENTER TRANSFORMER C		RUCTION \		T	
Core Type	EE25		EE25	5.44	User-Selected transformer core
Core		EE25		P/N:	PC40EE25-Z
Bobbin		ı	EE25_BOBBIN		EE25_BOBBIN
AE				cm^2	Core Effective Cross Sectional Area
LE			7.34		Core Effective Path Length
AL			1420	nH/T^2	Ungapped Core Effective Inductance

M. 1.00 1 mm Safety Margin Width (Half the Primary to Secondary Creepage Distance) L. 2.00 2 Number of Primary Layers NS 7 7 Number of Secondary Turns  DC INPUT VOLTAGE PARAMETERS VMIN 375 Volts Minimum DC Input Voltage WMAX 375 Volts Maximum DC Input Voltage  CURRENT WAVEFORM SHAPE PARAMETERS  DURY Ratio at full load, minimum primary inductance and minimum input voltage Average Primary Current RR 0.3075 Amps Primary Explore Current RR 0.3375 Amps Primary Explore Current RRMS 0.33 Amps Primary RMS Current  RRMS 0.33 Amps Primary RMS Current  TRANSFORMER PRIMARY DESIGN PARAMETERS  LP 1050 UHenries Typical Primary Inductance. +/- 10% to ensure a minimum primary inductance of 954 uH Primary inductance tolerance  P 10,00 10 % Primary Inductance tolerance  P 2745 Gauss Typical Primary Inductance of 954 uH Primary inductance tolerance  P 2745 Gauss Maximum Operating Flux Density, BM-3000 is recommended to Peak)  BM 22745 Gauss Relative Permeability of Ungapped Core Gapped Core Effective Inductance  Maximum Operating Flux Density, BM-3000 is recommended to Peak)  BWE 0.01 Imm Gap Length (Lg 9.0.1 mm)  BWE 0.053 Relative Permeability of Ungapped Core Gap Length (Lg 9.0.1 mm)  BWE 0.054 Maximum Finary Wire Gauge (Rounded to next smaller standard AWG value)  CM 81 Cmils Bare conductor diameter  LINEAUS AWG 23 AWG Secondary Current Secondary Current Secondary Gause Conductor mils Primary Wire Gauge (Rounded to next smaller standard AWG value)  P 2476 Cmis Amps Secondary Current Secondary Green Capacity (200 < CMA < 500)  TRANSFORMER SECONDARY DESIGN PARAMETERS  Lumped parameters  SP 4.07 Amps Secondary Current Secondary Gurent Capacity (200 < CMA < 500)  TRANSFORMER SECONDARY DESIGN PARAMETERS  Lumped parameters  SP 4.07 Amps Secondary Wire Gauge (Rounded up to next larger standard AWG value)  WOLTAGE STRESS PARAMETERS  VDRAIN Berecondary Current Capacity Capacit	BW		40.0	mm	Robbin Dhysical Winding Width
Creepage Distance    Creepage Distance		4.00			Bobbin Physical Winding Width
DC   Number of Primary Layers	IVI	1.00	1	mm	
DC INPUT VOLTAGE PARAMETERS VMIN 79 Voits Maximum DC Input Voltage  CURRENT WAVEFORM SHAPE PARAMETERS DMAX 0.59 Duty Ratio at full load, minimum primary inductance and minimum input voltage AVG 0.24 Amps Average Primary Current P 0.5120 Amps Minimum Pack Primary Current RR 0.3075 Amps Primary Ripple Current RRMS 0.33 Amps Primary Ripple Current RRMS 0.33 Amps Primary Ripple Current RRMS 0.33 Amps Primary Ripple Current RRANSFORMER PRIMARY DESIGN PARAMETERS LP 1050 Unternites Typical Primary Inductance of 954 uH P 10.5120 Amps Primary Inductance of 954 uH P 10.5120 Amps Primary Inductance of 954 uH R 10.500 Unternites Typical Primary Inductance of 954 uH R 10.500 Unternites Typical Primary Inductance of 954 uH R 10.500 Unternites Typical Primary Inductance of 954 uH R 10.500 Unternites Typical Primary Inductance of 954 uH R 10.500 Unternites Typical Primary Inductance of 954 uH R 10.500 Unternites Typical Primary Inductance of 954 uH R 10.500 Unternites Typical Primary Inductance of 954 uH R 10.500 Unternites Typical Primary Inductance of 954 uH R 10.500 Unternites Typical Primary Inductance of 954 uH R 10.500 Unternites Typical Primary Inductance of 954 uH R 10.500 Unternites Typical Primary Inductance of 954 uH R 10.500 Unternites Typical Primary Inductance of 954 uH R 10.500 Unternite Typical Primary Inductance of 954 uH R 10.500 Unternite Typical Primary Inductance of 954 uH R 10.500 Unternite Typical Primary Inductance of 954 uH R 10.500 Unternite Typical Primary Inductance of 954 uH R 10.500 Unternite Typical Primary Inductance of 954 uH R 10.500 Unternite Typical Primary Inductance of 954 uH R 10.500 Unternite Typical Primary Inductance of 954 uH R 10.500 Unternite Typical Primary Inductance of 954 uH R 10.500 Unternite Typical Primary Inductance of 954 uH R 10.500 Unternite Typical Primary Inductance of 954 uH R 10.500 Unternite Typical Primary Inductance of 954 uH R 10.500 Unternite Typical Primary Un	1	2.00	0		
DC INPUT VOLTAGE PARAMETERS VMIN 79 Volts Maximum DC Input Voltage  Duty Ratio at full load, minimum primary inductance and minimum input voltage Average Primary Current R 0.5120 Amps Primary Ripple Current R MS 0.33 Amps Primary Ripple Current R MS 0.33 Amps Primary Ring Current R MS 0.33 Amps Primary Ring Current Typical Primary Inductance +/- 10% to ensure a minimum primary inductance of 954 uH Primary inductance tolerance NP 1050 WHenries Typical Primary Inductance tolerance Primary Minding Number of Turns ACF liux Density for Core Loss Curves (0.5 X Peak to Peak)  PR ACF liux Density for Core Loss Curves (0.5 X Peak to Peak)  PR Relative Permeability of Ungapped Core Relative Permeabi	L NC				Number of Primary Layers
Minimum DC Input Voltage	NS	1	/		Number of Secondary Turns
Minimum DC Input Voltage	DC INDUT V	OLTAGE DADAMETE	D.C.		
CURRENT WAVEFORM SHAPE PARAMETERS  DMAX  0.59  Duty Ratio at full load, minimum primary inductance and minimum input voltage  AVG  0.24 Amps Average Primary Current  No.5120 Amps Average Primary Current  No.5120 Amps Minimum Peak Primary Current  Perimary Ripple Current  Reverage Primary Ripple Current  No.3075 Amps Primary Ripple Current  TRANSFORMER PRIMARY DESIGN PARAMETERS  LP TOLERANCE  10.00  10  10  10  10  10  10  10  10		OLIAGE PARAMETE		Volto	Minimum DC Innut Valtage
CURRENT WAVEFORM SHAPE PARAMETERS  DMAX  0.59  Duty Ratio at full load, minimum primary inductance and minimum input voltage Average Primary Current P 0.5120 Amps R 0.3075 Amps R 0.3075 Amps R Minimum Peak Primary Current R R R R R R R R R R R R R R R R R R R					Maximum DC Input Voltage
DMAX	VIMAX		3/5	VOITS	Maximum DC Input Voltage
DMAX					
AVG 0.24 Amps Average Primary Current P 0.5120 Amps Minimum Peak Primary Current R 0.3075 Amps Primary Ripple Current RMS 0.337 Amps Primary RMS Current RMS 0.333 Amps Primary RMS Current RANSFORMER PRIMARY DESIGN PARAMETERS LP 1050 UHenries Typical Primary Inductance +/- 10% to ensure a minimum primary inductance of 954 uH Primary I		HAPE PARAMETERS			D. D. C. (CIII. I. C.
AVG   0.24   Amps   0.5410   Amps   0.5120   Amps   Current   P   0.5120   Amps   Amps   Current   R   0.3075   Amps   Primary Current   R   0.3075   Amps   Primary Ripple Current   R   0.3075   Amps   Primary Ripple Current   R   0.3075   Amps   Primary Ripple Current   R   R   0.3075   Amps   Primary Rimary Current   R   R   R   R   R   R   R   R   R	DMAX		0.59		
P	14)/0		0.04	A	
RMS 0.3075 Amps Primary Ripole Current RMS 0.33 Amps Primary RMS Current  RANSFORMER PRIMARY DESIGN PARAMETERS  LP TOLERANCE 10.00 10 % Primary Inductance of 954 uH  LP TOLERANCE 10.00 10 % Primary Inductance of 954 uH  LP TOLERANCE 339 InH/T/2 Gapped Core Effective Inductance BM 2745 Gauss Maximum Operating Flux Density, BM         Typical Primary Inductance of 954 uH  Primary Winding Number of Turns  ALG 339 InH/T/2 Gapped Core Effective Inductance  BAC 824 Gauss AC Flux Density for Core Loss Curves (0.5 X Peak to Peak)  Ur 2053 Relative Permeability of Ungapped Core  G 0.111 mm Gap Length (Lg > 0.1 mm)  BWE 16.4 mm Effective Bobbin Width  DD 0.295 mm Maximum Primary Wire Diameter including insulation  INS 0.05 mm Estimated Total Insulation Thickness (= 2 * film thickness)  DIA 0.243 mm Bare conductor diameter  AWG 311 AWG Primary Wire Gauge (Rounded to next smaller standard AWG value)  CM 81 Cmils Bare conductor effective area in circular mils  CMA 247 Cmils/Amp Primary Winding Current Capacity (200 < CMA < 500)  TRANSFORMER SECONDARY DESIGN PARAMETERS  Lumped parameters  SP 4.07 Amps Peak Secondary Current  SRPS 4.07 Amps Secondary Bare Conductor minimum circular mils  PRIPPLE 1.90 Amps Secondary Bare Conductor minimum circular mils  Secondary Wire Gauge (Rounded up to next larger standard AWG value)  VOLTAGE STRESS PARAMETERS  VDRAIN 607 Volts Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)					
RMS					
Transformer Primary Design Parameters					Primary Rippie Current
LP   1050 uHenries   Typical Primary Inductance. +/- 10% to ensure a minimum primary inductance of 954 uH   P_TOLERANCE   10.00   10 % Primary inductance tolerance   NP   56   Primary inductance tolerance   NP   56   Primary Winding Number of Turns   ALG   339 nH/T^2   Gapped Coef Effective Inductance   BM   2745   Gauss   Maximum Operating Flux Density, BM<3000 is recommended   NP   2053   Relative Permeability of Ungapped Core   LG   0.11 mm   Gap Length (Lg > 0.1 mm)   BWE   16.4 mm   Effective Bobbin Width   DD   0.295 mm   Maximum Primary Wire Diameter including insulation   NS   0.05 mm   Estimated Total Insulation Thickness (= 2 * film thickness)   NS   0.05 mm   Bare conductor diameter   AWG   31   AWG   Primary Wire Gauge (Rounded to next smaller standard AWG value)   CM   81   Cmils   Bare conductor effective area in circular mils   CMA   247   Cmils/Amp   Peak Secondary Wirended   RIPPLE   1.90   Amps   Output Capacitor RMS Ripple Current   SRMS   2.15   Amps   Secondary RMS Current   RIPPLE   1.90   Amps   Output Capacitor RMS Ripple Current   SRMS   2.3   AWG   Secondary RMS Current   SRMS   2.4   Amps   Secondary RMS Current   SRMS   2.5   Amps   Secondary RMS Current   SRMS   2.5   Amps   Secondary RMS Current   SRMS   3   AWG   Secondary RMS Current   SR	IRMS		0.33	Amps	Primary RMS Current
LP   1050 uHenries   Typical Primary Inductance. +/- 10% to ensure a minimum primary inductance of 954 uH   P_TOLERANCE   10.00   10 % Primary inductance tolerance   NP   56   Primary inductance tolerance   NP   56   Primary Winding Number of Turns   ALG   339 nH/T^2   Gapped Coef Effective Inductance   BM   2745   Gauss   Maximum Operating Flux Density, BM<3000 is recommended   NP   2053   Relative Permeability of Ungapped Core   LG   0.11 mm   Gap Length (Lg > 0.1 mm)   BWE   16.4 mm   Effective Bobbin Width   DD   0.295 mm   Maximum Primary Wire Diameter including insulation   NS   0.05 mm   Estimated Total Insulation Thickness (= 2 * film thickness)   NS   0.05 mm   Bare conductor diameter   AWG   31   AWG   Primary Wire Gauge (Rounded to next smaller standard AWG value)   CM   81   Cmils   Bare conductor effective area in circular mils   CMA   247   Cmils/Amp   Peak Secondary Wirended   RIPPLE   1.90   Amps   Output Capacitor RMS Ripple Current   SRMS   2.15   Amps   Secondary RMS Current   RIPPLE   1.90   Amps   Output Capacitor RMS Ripple Current   SRMS   2.3   AWG   Secondary RMS Current   SRMS   2.4   Amps   Secondary RMS Current   SRMS   2.5   Amps   Secondary RMS Current   SRMS   2.5   Amps   Secondary RMS Current   SRMS   3   AWG   Secondary RMS Current   SR		V DEGIGNI DADAMET			
Minimum primary inductance of 954 uH		Y DESIGN PARAMET		الما المسامر	Timical Drive and Industrian and 1 400/ to a second
P_TOLERANCE   10.00   10 %   Primary inductance tolerance   NPP   56   56   Primary Winding Number of Turns   339 nH/T^2   Gapped Core Effective Inductance   BM   2745   Gauss   Maximum Operating Flux Density, BM	LP		1050	uHenries	
Search	LD TOLEDANIOE	40.00	40	0.1	
ALG BM BM BAC		10.00			
BM 2745 Gauss Maximum Operating Flux Density, BM<3000 is recommended and to recommended and to Peak an					
BAC 824 Gauss recommended AC Flux Density for Core Loss Curves (0.5 X Peak to Peak)  BAC 9263 Relative Permeability of Ungapped Core Gap Length (Lg > 0.1 mm)  BWE 964 Gap Length (Lg > 0.1 mm)  BWE 965 Gap Length (Lg > 0.1 mm)  BWIGHT Maximum Primary Wire Diameter including insulation  INS 965 Maximum Primary Wire Diameter including insulation Thickness (= 2 * film thickness)  DIA 965 Maximum Primary Wire Gauge (Rounded to next smaller standard AWG value)  BAWG 976 Primary Wire Gauge (Rounded to next smaller standard AWG value)  CM 976 Maximum Primary Wire Gauge (Rounded to next smaller standard AWG value)  CM 976 Maximum Primary Wire Gauge (Rounded to next smaller standard AWG value)  CM 977 Maximum Viriading Current Capacity (200 < CMA < 500)  TRANSFORMER SECONDARY DESIGN PARAMETERS  Lumped parameters  ISP 976 4.07 Amps Peak Secondary Current  SRMS 977 Amps Secondary RMS Current  SRMS 977 Amps Output Capacitor RMS Ripple Current  CMS 977 Amps Output Capacitor RMS Ripple Current  CMS 977 Amps Output Capacitor RMS Ripple Current  CMS 978 Cmills Secondary Bare Conductor minimum circular mils  Secondary Bare Conductor minimum circular mils  Secondary Wire Gauge (Rounded up to next larger standard AWG value)  VOLTAGE STRESS PARAMETERS  VDRAIN 607 Volts Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)					Gapped Core Effective Inductance
Record   R	ВМ		2745	Gauss	
10 Peak   10 P	D.4.0		20.4		
LG	BAC		824	Gauss	
LG	ur		2053		
BWE 0D 0.295 mm Effective Bobbin Width 0.295 mm Maximum Primary Wire Diameter including insulation insulation 0.05 mm Estimated Total Insulation Thickness (= 2 * film thickness) DIA 0.243 mm Bare conductor diameter AWG 9					Con Longth (La > 0.1 mm)
DD  OD  OD  OD  OD  OD  OD  OD  OD  OD					
insulation  INS  INS  INS  INS  INS  INS  INS  IN					
DIA	OD		0.293	111111	
DIA 0.243 mm Bare conductor diameter AWG 31 AWG Primary Wire Gauge (Rounded to next smaller standard AWG value) CM 81 Cmils Bare conductor effective area in circular mils CMA 247 Cmils/Amp Primary Winding Current Capacity (200 < CMA < 500)  TRANSFORMER SECONDARY DESIGN PARAMETERS Lumped parameters ISP 4.07 Amps Peak Secondary Current ISP SRMS 2.15 Amps Secondary RMS Current IRIPPLE 1.90 Amps Output Capacitor RMS Ripple Current CMS 430 Cmils Secondary Bare Conductor minimum circular mils AWGS 23 AWG Secondary Wire Gauge (Rounded up to next larger standard AWG value)  VOLTAGE STRESS PARAMETERS VDRAIN 607 Volts Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)	INS		0.05	mm	
AWG  AWG  AWG  AWG  AWG  AWG  AWG  AWG			0.00		
Standard AWG value	DIA		0.243	mm	Bare conductor diameter
Standard AWG value	AWG		31	AWG	Primary Wire Gauge (Rounded to next smaller
CMA  247 Cmils/Amp Primary Winding Current Capacity (200 < CMA < 500)  TRANSFORMER SECONDARY DESIGN PARAMETERS  Lumped parameters  ISP  4.07 Amps Peak Secondary Current  ISRMS  2.15 Amps Secondary RMS Current  IRIPPLE  1.90 Amps Output Capacitor RMS Ripple Current  CMS  430 Cmils Secondary Bare Conductor minimum circular mils  Secondary Wire Gauge (Rounded up to next larger standard AWG value)  VOLTAGE STRESS PARAMETERS  VDRAIN  607 Volts Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)					
TRANSFORMER SECONDARY DESIGN PARAMETERS  Lumped parameters ISP 4.07 Amps Peak Secondary Current SERMS Secondary RMS Current IRIPPLE 1.90 Amps Output Capacitor RMS Ripple Current CMS 430 Cmils Secondary Bare Conductor minimum circular mils Secondary Wire Gauge (Rounded up to next larger standard AWG value)  VOLTAGE STRESS PARAMETERS VDRAIN 607 Volts Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)	CM				Bare conductor effective area in circular mils
TRANSFORMER SECONDARY DESIGN PARAMETERS  Lumped parameters  ISP	CMA		247	Cmils/Amp	
Lumped parameters  ISP					500)
Lumped parameters  ISP					
SP		PARY DESIGN PARAM	IETERS	1	
ISRMS  2.15 Amps Secondary RMS Current  1.90 Amps Output Capacitor RMS Ripple Current  2.00 Cmils Secondary Bare Conductor minimum circular mils  2.00 Awg Secondary Wire Gauge (Rounded up to next larger standard AWG value)  2.00 VOLTAGE STRESS PARAMETERS  2.15 Amps Secondary RMS Current  2.16 Amps Output Capacitor RMS Ripple Current  2.17 Secondary Wire Gauge (Rounded up to next larger standard AWG value)  2.18 Amps Secondary RMS Current  3.19 Secondary Bare Conductor minimum circular mils  4.20 Secondary Wire Gauge (Rounded up to next larger standard AWG value)  4.20 VOLTAGE STRESS PARAMETERS  4.21 VOLTAGE STRESS PARAMETERS  4.22 VOLTAGE STRESS PARAMETERS  4.23 VOLTAGE STRESS PARAMETERS  4.24 VOLTAGE STRESS PARAMETERS  4.25 VOLTAGE STRESS PARAMETERS  4.26 VOLTAGE STRESS PARAMETERS  4.27 VOLTAGE STRESS PARAMETERS  4.27 VOLTAGE STRESS PARAMETERS  4.28 VOLTAGE STRESS PARAMETERS  4.29 VOLTAGE STRESS PARAMETERS  4.20 VOLTAGE STRESS PARAMETERS				<b> </b>	
IRIPPLE  1.90 Amps Output Capacitor RMS Ripple Current CMS AWGS  23 AWG Secondary Bare Conductor minimum circular mils Secondary Wire Gauge (Rounded up to next larger standard AWG value)  VOLTAGE STRESS PARAMETERS VDRAIN  607 Volts Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)					
CMS 430 Cmils Secondary Bare Conductor minimum circular mils Secondary Wire Gauge (Rounded up to next larger standard AWG value)  VOLTAGE STRESS PARAMETERS  VDRAIN 607 Volts Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)					
AWGS  23 AWG  Secondary Wire Gauge (Rounded up to next larger standard AWG value)  VOLTAGE STRESS PARAMETERS  VDRAIN  607 Volts  Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)	IRIPPLE		1.90	Amps	Output Capacitor RMS Ripple Current
VOLTAGE STRESS PARAMETERS  VDRAIN  607 Volts  Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)	CMS				
VOLTAGE STRESS PARAMETERS  VDRAIN  607 Volts  Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)	AWGS		23	AWG	
VDRAIN  607 Volts  Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)					standard AWG value)
VDRAIN  607 Volts  Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)					
VDRAIN  607 Volts  Maximum Drain Voltage Estimate (Assumes 20% zener clamp tolerance and an additional 10% temperature tolerance)	<b>VOLTAGE STRESS PARA</b>	METERS			
zener clamp tolerance and an additional 10% temperature tolerance)	VDRAIN		607	Volts	Maximum Drain Voltage Estimate (Assumes 20%
					zener clamp tolerance and an additional 10%
PIVS 59 Volts Output Rectifier Maximum Peak Inverse Voltage					temperature tolerance)
	PIVS		59	Volts	Output Rectifier Maximum Peak Inverse Voltage

#### 9 Performance Data

The ON/OFF control scheme employed by *TinySwitch-III* yields virtually constant efficiency across the 25% to 100% load range required for compliance with EPA, CEC, CECP and AGO energy efficiency standards for external power supplies (EPS). Even at loads below 10% of the supply's full rated output power, efficiency remains above 65%, providing excellent standby performance for applications that require it. This performance is automatic with ON/OFF control. There are no special burst modes that require the designer to consider specific thresholds within the load range in order to achieve compliance with global energy efficiency standards.

All measurements performed at room temperature, 60 Hz input frequency.

### 9.1 Efficiency

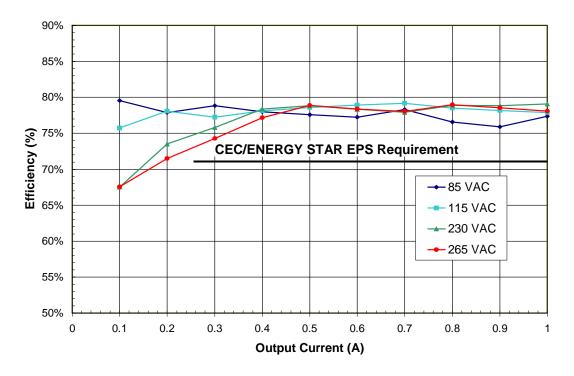


Figure 6 – Efficiency vs. Output Current, Room Temperature, 60 Hz.

#### 9.2 Active Mode CEC Measurement Data

In the state of California, after July 1, 2006, all single-output EPS adapters – including those sold with the products they power – must meet the California Energy Commission (CEC) requirement for minimum active-mode efficiency and no-load input power consumption. Minimum active-mode efficiency is defined as the average efficiency at 25, 50, 75 and 100% of rated output power printed on the nameplate of the supply:

Nameplate Output (P <sub>o</sub> )	Minimum Efficiency in Active Mode of Operation
< 1 W	$0.49 \times P_O$
≥ 1 W to ≤ 49 W	$0.09 \times \ln (P_0) + 0.49$ [ln = natural log]
> 49 W	0.84 W

For adapters that are single input voltage only, the measurements are to be made at the nominal rated input voltage (115 VAC or 230 VAC). For universal input adapters, the measurements are to be made at both nominal input voltages (115 VAC and 230 VAC).

To comply with the standard, the average of the four efficiency measurements must be greater than or equal to the efficiency specified by the standard.

Percent of Full Load	Efficiency (%)				
	115 VAC	230 VAC			
25	75	74.5			
50	78.5	78.8			
75	78.8	78.5			
100	78	79.1			
Average	77.6	77.7			
Required CEC minimum average efficiency (%)	71.3				

From these results it is apparent that the efficiency of this design easily exceeds the required 71.3 %. More states within the USA, and many other countries around the world are adopting similar energy efficiency standards (based on the original Energy Star standard). For the latest, up-to-date information on energy efficiency regulations, please visit the PI Green Room, at:

http://www.powerint.com/greenroom/regulations.htm



# 9.3 No-load Input Power (R8 not installed: no bias winding supplementation)

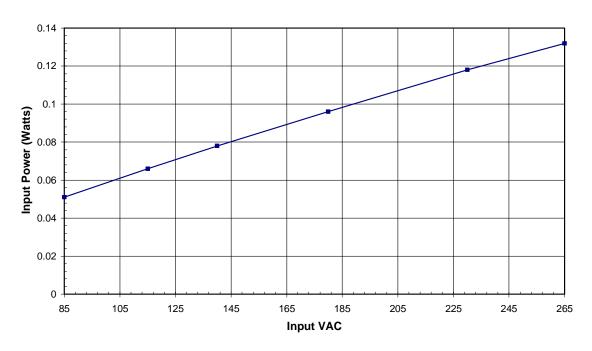


Figure 7 – No-load Input Power vs. Input Line Voltage, Room Temperature, 60 Hz.

# 9.4 No-load Input Power (with R8 and bias winding supplementation)

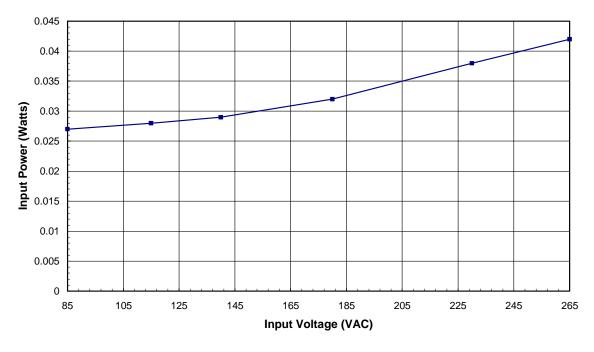


Figure 8 - No-load Input Power vs. Input Line Voltage, Room Temperature, 60 Hz, with Bias Winding.

## 9.5 Available Standby Output Power

The chart below shows the available output power versus line voltage at input power consumption levels of 1, 2 and 3 watts (respectively). Again, this performance illustrates the value of ON/OFF control, as it automatically maintains a high efficiency, even during very light loading. This simplifies complying with standby requirements that specify that a fair amount of power be available to the load at low input power consumption levels. The *TinySwitch-III* ON/OFF control scheme maximizes the amount of output power available to the load in standby operation when the allowable input power is fixed at a low value. This simplifies the design of products such as printers, set-top boxes, DVD players, etc. that must meet stringent standby power consumption requirements.

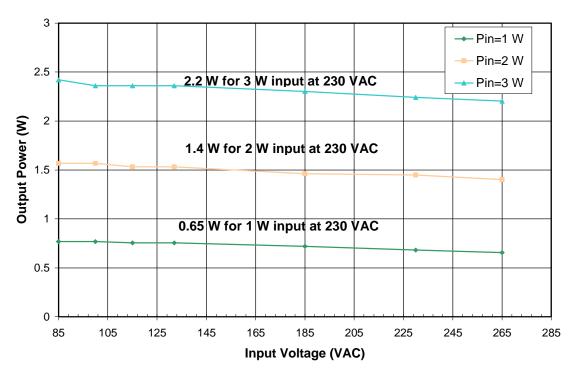


Figure 9 – Available Output Power for 1, 2 and 3 Watts of Input Power.

# 9.6 Regulation

# 9.6.1 Load and Line

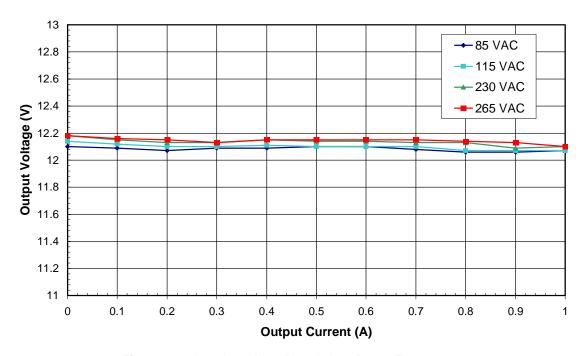


Figure 10 – Load and Line Regulation, Room Temperature.

#### 10 Thermal Performance

Temperature measurements of key components were taken using T-type thermocouples. The thermocouples were soldered directly to a SOURCE pin of the TNY278P device and to the cathode of the output rectifier. The thermocouples were glued to the output capacitor and to the external core and winding surfaces of transformer T1.

The unit was sealed inside a large box to eliminate any air currents. The box was placed inside a thermal chamber. The ambient temperature within the large box was raised to 50 °C. The unit was then operated at full load and the temperature measurements were taken after they stabilized for 1 hour at 50 °C.

Temperature (°C)				
Item	85 VAC	265 VAC		
Ambient	50 <sup>*</sup>	50 <sup>*</sup>		
TNY278P (U1)	96.1	92.8		
Transformer (T1)	77.8	80		
Output Rectifier (D7)	101	100		
Output Capacitor (C10)	68.2	66.8		

<sup>\*</sup>To simulate operation inside sealed enclosure at 40 °C external ambient.

These results show that all key components have an acceptable rise in temperature.

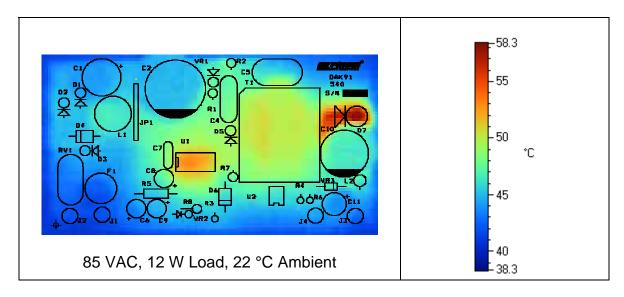


Figure 11 – Infrared Thermograph of Open Frame Operation, at Room Temperature.

# 11 Waveforms

# 11.1 Drain Voltage and Current, Normal Operation

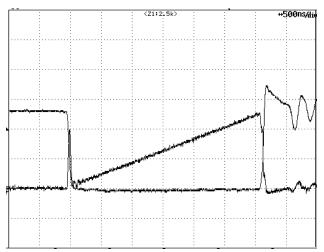


Figure 12 - 115 VAC, Full Load.

 $\begin{array}{l} \mbox{Upper: } I_{DRAIN}, \ 0.1 \ \mbox{A / div.} \\ \mbox{Lower: } V_{DRAIN}, \ 50 \ \mbox{V}, \ 500 \ \mbox{ns / div.} \end{array}$ 

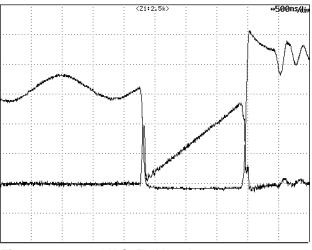


Figure 13 – 230 VAC, Full Load.

Upper:  $I_{DRAIN}$ , 0.1 A / div. Lower:  $V_{DRAIN}$ , 100 V / div.

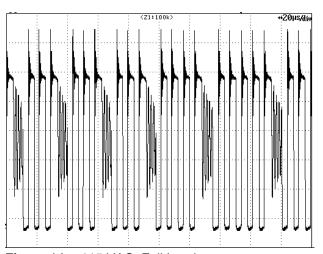


Figure 14 - 115 VAC, Full Load. V<sub>DRAIN</sub>, 50 V, 20  $\mu$ s / div.

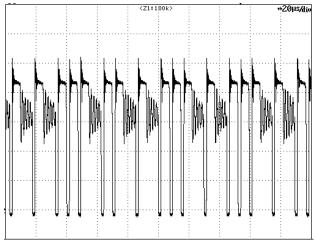


Figure 15 – 230 VAC, Full Load.  $V_{DRAIN},\,100~V,\,20~\mu s~/~div.$ 

# 11.2 Output Voltage Start-Up Profile

Start-up into full resistive load and no-load were both verified. A 12  $\Omega$  resistor was used for the load, to maintain 1 A under steady-state conditions.



Figure 16 – Start-Up Profile, 115 VAC. Fast trace is no-load rise time Slower trace is maximum load (12  $\Omega$ ) 2 V, 5 ms / div.

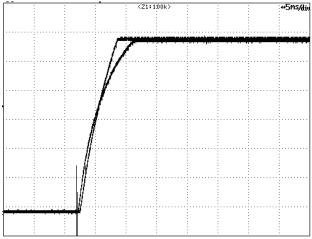


Figure 17 - Start-Up Profile, 230 VAC. Fast trace is no-load rise time Slower trace is maximum load (12  $\Omega$ ) 2 V, 5 ms / div.

# 11.3 Drain Voltage and Current Start-Up Profile

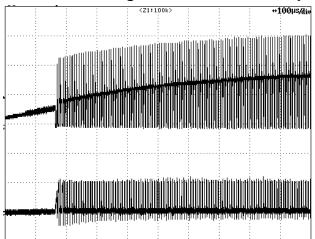


Figure 18 – 90 VAC Input and Maximum Load. Upper: V<sub>DRAIN</sub>, 100 V & 100 μs / div. Lower: I<sub>DRAIN</sub>, 0.5 A / div.

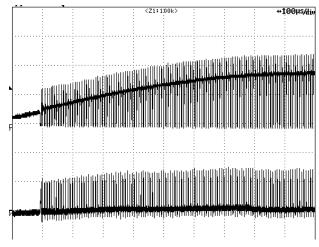
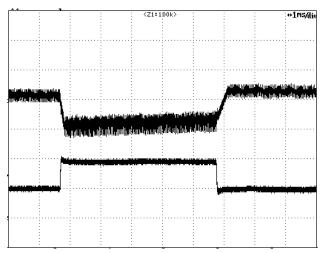


Figure 19 – 265 VAC Input and Maximum Load. Upper:  $V_{DRAIN}$ , 200 V & 100  $\mu s$  / div. Lower: I<sub>DRAIN</sub>, 0.5 A / div.

# 11.4 Load Transient Response (75% to 100% Load Step)



<21:100k> →1πs/dia

Figure 20 – Transient Response, 115 VAC, 50-100-50% Load Step. Upper: V<sub>OUT</sub> 50 mV/div. Lower: I<sub>OUT</sub> 0.5 A, 1 ms / div.

Figure 21 – Transient Response, 230 VAC, 50-100-50% Load Step. Upper: V<sub>OUT</sub> 50 mV/div. Lower: I<sub>OUT</sub> 0.5 A, 1 ms / div.

# 11.5 Output Ripple Measurements

### 11.5.1 Ripple Measurement Technique

A modified oscilloscope test probe was used to take output ripple measurements, in order to reduce the pickup of spurious signals. Using the probe adapter pictured in Figure 22, the output ripple was measured with a 1  $\mu$ F electrolytic, and a 0.1  $\mu$ F ceramic capacitor connected as shown.

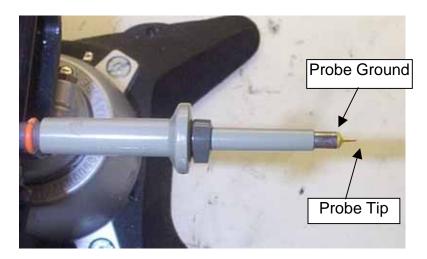
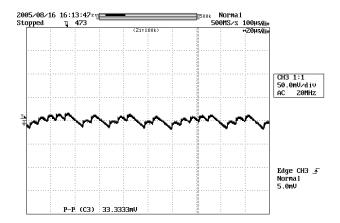
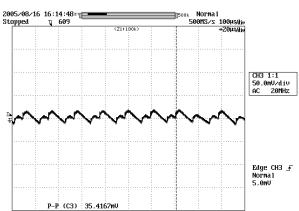




Figure 22 – Oscilloscope Probe Prepared for Ripple Measurement (End Cap and Ground Lead Removed).

#### 11.5.2 Measurement Results





**Figure 23** – Ripple, 85 VAC, Full Load. 20 µs, 50 mV / div.

Figure 24 – Ripple, 115 VAC, Full Load. 20 μs, 50 mV / div.

# 11.6 Overvoltage Shutdown

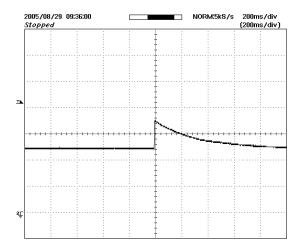


Figure 25 – Overvoltage Shutdown. 265 VAC, No Load. 50 ms, 5 V / div.

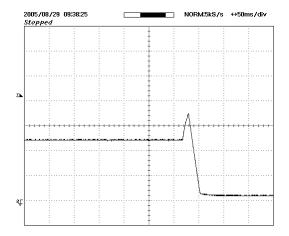


Figure 26 – Overvoltage Shutdown. 265 VAC, Full Load. 50 ms, 5 V / div.

# 12 Line Surge

Differential input line surge (1.2/50  $\mu$ s) testing was completed on a single test unit to IEC61000-4-5. Input voltage was set at 230 VAC / 60 Hz. Output was loaded at full load and operation was verified following each surge event.

Surge Voltage	Phase Angle	Generator Impedance	Number of Strikes	Test Result
1 kV Differential	90°	2 Ω	10	PASS
2 kV Common Mode	90°	12 Ω	10	PASS

Unit passed under all test conditions.

#### 13 Conducted EMI

Conducted emissions tests were performed at 115 VAC and 230 VAC at full load (12 V, 1 A). Measurements were taken with an Artificial Hand connected and a floating DC output load resistor. A DC output cable was included.

Composite EN55022B / CISPR22B conducted limits are shown. In all cases there was excellent (>10 dB) margin.

## 13.1 115 VAC, Full Load

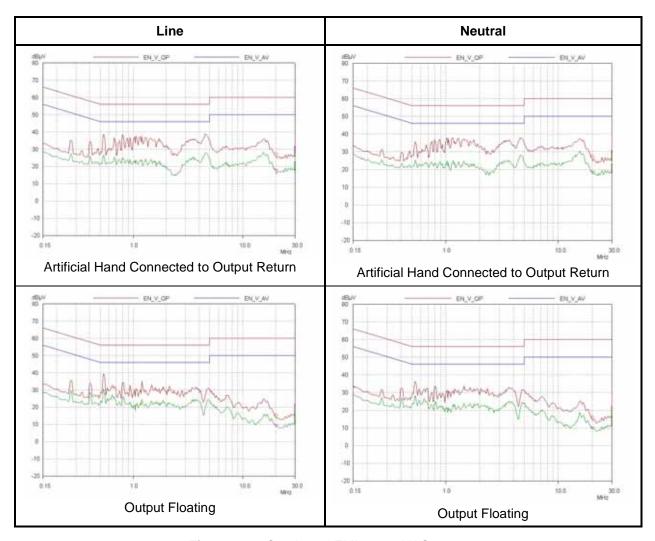


Figure 27 — Conducted EMI at 115 VAC.

# 13.2 230 VAC, Full Load

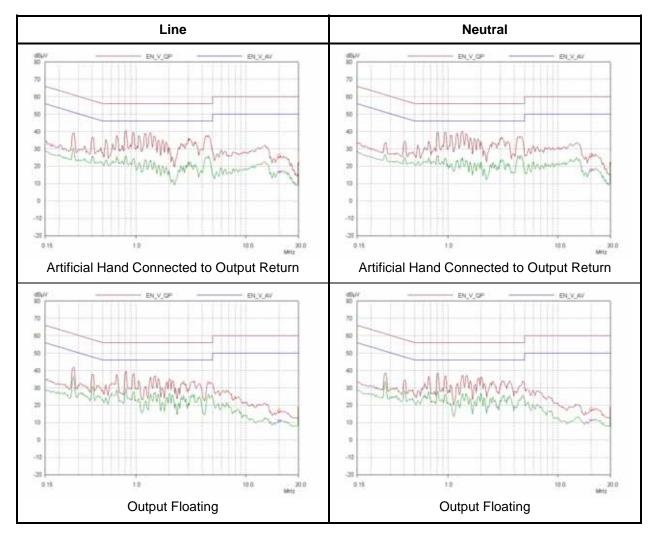


Figure 28 — Conducted EMI at 230 VAC.

#### 14 Audible Noise

An open-frame (no enclosure) unit was tested with an Audio Precision Analyzer, using a microphone positioned one inch from the core of transformer T1. The test was done with the unit in an acoustically isolated and dampened chamber. The load was adjusted until a maximum reading was obtained.

35 dBrA is considered the acceptable limit for frequencies below 18 kHz. An enclosure will typically further reduce measurable acoustic noise levels by an additional 10 dBrA.

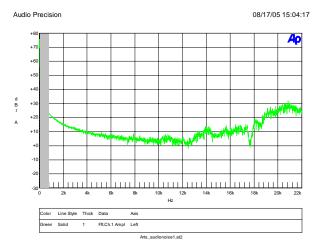


Figure 29 – Audible Noise  $V_{IN}$  = 120 VAC;  $I_{OUT}$  = 350 mA.



Figure 30 – Audible Noise  $V_{IN} = 120 \text{ VAC}$ ;  $I_{OUT} = 1 \text{ A}$ .



Figure 31 – Audible Noise  $V_{IN} = 230 \text{ VAC}$ ;  $I_{OUT} = 1 \text{ A}$ .



Figure 32 – Audible Noise  $V_{IN}$  = 230 VAC;  $I_{OUT}$  =1.2 A.

Note: Shaded area obscured due to ambient noise.

# 15 Extended and Reduced Current Limit (I<sub>LIMIT</sub>) Operation

Additional capacitors (C8 and C9 on the BOM in Section 6) have been included in the DAK-91 kit for the convenience of trying out the  $I_{\text{LIMIT}}+1$  and  $I_{\text{LIMIT}}-1$  operation of TNY278 in the EP-91 reference board. When C7 (0.1  $\mu$ F) is replaced with a 10  $\mu$ F capacitor (C9), the TNY278 will operate in the  $I_{\text{LIMIT}}+1$  mode, which increases the maximum primary current limit from the standard maximum limit of 0.55 A to 0.65 A (equal to that of a TNY279). This allows a TNY278 to deliver from 15% to 25% more output power (depending on the output voltage and current).

**CAUTION:** Because EP-91 was designed for standard I<sub>LIMIT</sub> operation, It should not be loaded with more than 1.25 A at an elevated temperature for very long (a few minutes) when verifying the performance of TNY278 in the I<sub>LIMIT</sub>+1 mode, since the other power components (transformer, input bulk capacitors, output diode, output capacitors and primary clamp network) are not sized for sustained operation at more than 12 W.

When C7 is replaced with a 1  $\mu$ F capacitor (C8), the TNY278 will operate in the I<sub>LIMIT</sub>-1 mode, which reduces the maximum current limit from the standard maximum limit of 0.55 A to 0.45 A (equal to that of a TNY277). Although this reduces the maximum output power that the supply can deliver, it typically will increase the efficiency, especially at lower output power levels. To take the fullest advantage of the increase in efficiency that can be obtained from I<sub>LIMIT</sub>-1 operation, the power transformer would need to be redesigned slightly.

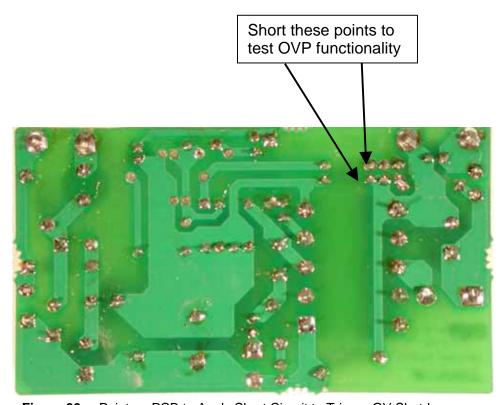
# 16 TNY277 and TNY279 Operation in EP-91

A TNY277 device used in the  $I_{LIMIT}+1$  mode (a 10  $\mu$ F installed in place of C7) will work in the EP-91 reference board, and deliver output power equal to that of a TNY278 device. This flexibility allows a design engineer the option of using a lower cost part in applications with less demanding thermal requirements.

A TNY279 device used in the  $I_{LIMIT}$ -1 mode (a 1  $\mu F$  installed in place of C7) will deliver the same output power as a TNY278 in the standard  $I_{LIMIT}$  configuration. This can improve efficiency and lower the temperature rise of the device, which can give greater thermal margin to a design that must operate in high ambient temperature environments.

# 17 OVP Operation Verification

While the EP-91 is in normal operation, monitor the output with a storage oscilloscope. To cause an overvoltage condition to occur, short circuit the optocoupler LED (as shown below) to open the feedback control loop. The oscilloscope will capture the output voltage rising until the increasing voltage across VR2 causes it to conduct, and the TNY278 device latches off. To reset the OVP latch, the AC input power must be removed long enough to allow the input bulk capacitors to fully discharge.



**Figure 33** — Point on PCB to Apply Short Circuit to Trigger OV Shutdown.

# **18 Revision History**

Date	Author	Revision	Description & changes
25-Jan-06	JAJ	1.0	Formatted for Final Release
07-Feb-06	JAJ	1.1	Formatted and corrected measurement scales / div.

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